

## OC81D Transistor Datasheet. Parameters and Characteristics.

Type Designator: OC81D

Material of transistor: Ge

Polarity: PNP

Maximum collector power dissipation ( $P_c$ ), W: 0.15

Maximum collector-base voltage [ $U_{cb}$ ], V: 16

Maximum collector-emitter voltage [ $U_{ce}$ ], V: 16

Maximum emitter-base voltage [ $U_{eb}$ ], V: 3

Maximum collector current [ $I_c$  max], A: 0.01

Maksimalna temperatura ( $T_j$ ), °C: 80

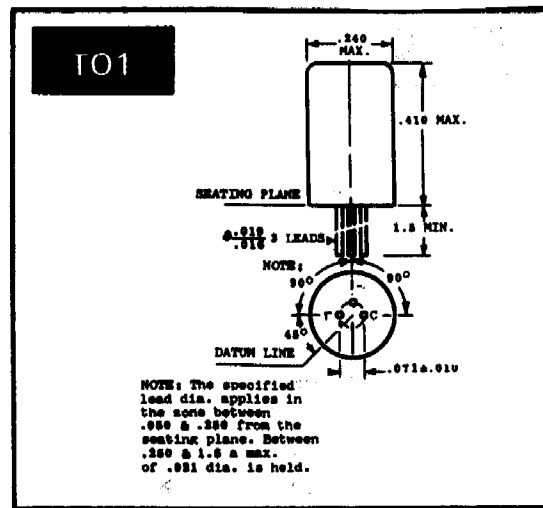
Transition frequency ( $f_t$ ), MHz: 0.2

Collector capacitance ( $C_c$ ), pF: 40

Forward current transfer ratio (hFE), min: 20

Noise Figure, dB: -

Package of OC81D transistor:



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